Switch-mode **Power Rectifier**

Features and Benefits

- Low Forward Voltage
- Low Power Loss/High Efficiency
- High Surge Capacity
- 175°C Operating Junction Temperature
- 16 A Total (8 A Per Diode Leg)
- These Devices are Pb-Free and are RoHS Compliant*

Applications

- Power Supply Output Rectification
- Power Management
- Instrumentation

Mechanical Characteristics

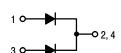
- Case: Epoxy, Molded
- Epoxy Meets UL 94 V-0 @ 0.125 in
- Weight: 1.9 Grams (Approximately)
- Finish: All External Surfaces Corrosion Resistant and Terminal Leads are Readily Solderable
- Lead Temperature for Soldering Purposes: 260°C Max. for 10 Seconds
- Human Body Model 3B • ESD Rating: Machine Model C



ON Semiconductor®

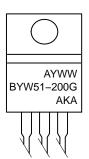
www.onsemi.com

ULTRAFAST RECTIFIER 16 AMPERES, 200 VOLTS $t_{rr} = 35 \text{ ns}$





MARKING DIAGRAM



= Assembly Location

TO-220

PLASTIC

= Year WW = Work Week BYW51-200 = Device Code = Pb-Free Package G AKA = Diode Polarity

ORDERING INFORMATION

Device	Package	Shipping
BYW51-200G	TO-220 (Pb-Free)	50 Units/Rail

^{*}For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V _{RRM} V _{RWM} V _R	200	V
Average Rectified Forward Current T _C = 156°C Per Leg Total Device	I _{F(AV)}	8.0 16	А
Peak Rectified Forward Current (Square Wave, 20 kHz), $T_C = 153^{\circ}C$ – Per Diode Leg	I _{FM}	16	А
Nonrepetitive Peak Surge Current (Surge applied at rated load conditions halfwave, single phase, 60 Hz)	I _{FSM}	100	А
Operating Junction Temperature and Storage Temperature	T _J , T _{stg}	-65 to +175	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL CHARACTERISTICS

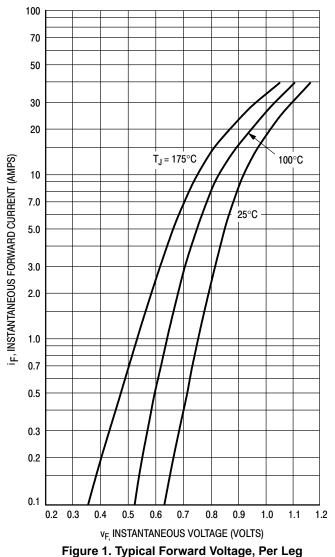
Characteristic	Conditions	Symbol	Value	Unit
Maximum Thermal Resistance, Junction-to-Case	Min. Pad	$R_{\theta JC}$	3.0	°C/W
Maximum Thermal Resistance, Junction-to-Ambient	Min. Pad	$R_{\theta JA}$	60.0	

ELECTRICAL CHARACTERISTICS

Characteristic	Symbol	Min	Typical	Max	Unit
Instantaneous Forward Voltage (Note 1) ($i_F = 8.0 \text{ A}, T_j = 100^{\circ}\text{C}$) ($i_F = 8.0 \text{ A}, T_j = 25^{\circ}\text{C}$)	VF	- -	0.8 0.89	0.89 0.97	V
Maximum Instantaneous Reverse Current (Note 1) (Rated dc Voltage, $T_j = 100^{\circ}\text{C}$) (Rated dc Voltage, $T_j = 25^{\circ}\text{C}$)	i _R	- -	21 3.8	1000 10	μΑ
Maximum Reverse Recovery Time $(I_F = 1.0 \text{ A}, \text{ di/dt} = 50 \text{ A/s})$ $(I_F = 0.5 \text{ A}, I_R = 1.0 \text{ A}, I_{REC} = 0.25 \text{ A})$	t _{rr}	_	-	35 25	ns

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

1. Pulse Test: Pulse Width = 300 s, Duty Cycle ≤ 2.0%



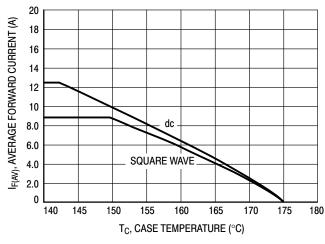


Figure 4. Current Derating, Case, Per Leg

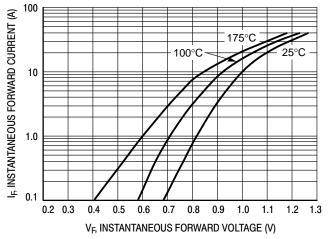


Figure 2. Maximum Forward Voltage

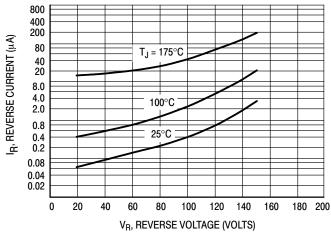


Figure 3. Typical Reverse Current, Per Leg*

^{*} The curves shown are typical for the highest voltage device in the voltage grouping. Typical reverse current for lower voltage selections can be estimated from these same curves if V_{R} is sufficiently below rated V_{R} .

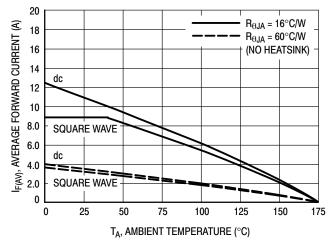


Figure 5. Current Derating, Ambient, Per Leg

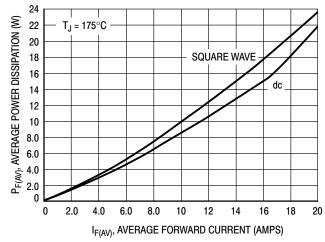


Figure 6. Power Dissipation, Per Leg

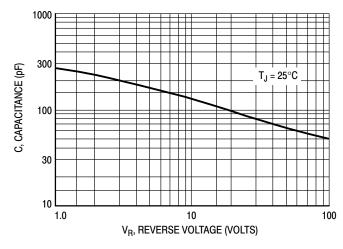
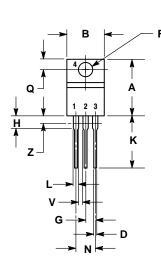
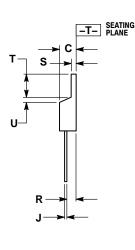


Figure 7. Typical Capacitance, Per Leg

PACKAGE DIMENSIONS

TO-220 CASE 221A-09 **ISSUE AH**





- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. CONTROLLING DIMENSION: INCH.
- DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE

	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
Α	0.570	0.620	14.48	15.75
В	0.380	0.415	9.66	10.53
С	0.160	0.190	4.07	4.83
D	0.025	0.038	0.64	0.96
F	0.142	0.161	3.61	4.09
G	0.095	0.105	2.42	2.66
Н	0.110	0.161	2.80	4.10
J	0.014	0.024	0.36	0.61
K	0.500	0.562	12.70	14.27
L	0.045	0.060	1.15	1.52
N	0.190	0.210	4.83	5.33
Q	0.100	0.120	2.54	3.04
R	0.080	0.110	2.04	2.79
S	0.045	0.055	1.15	1.39
T	0.235	0.255	5.97	6.47
U	0.000	0.050	0.00	1.27
٧	0.045		1.15	
Z		0.080		2.04

PIN 1. ANODE

- CATHODE 2.
- 3. ANODE
- CATHODE

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